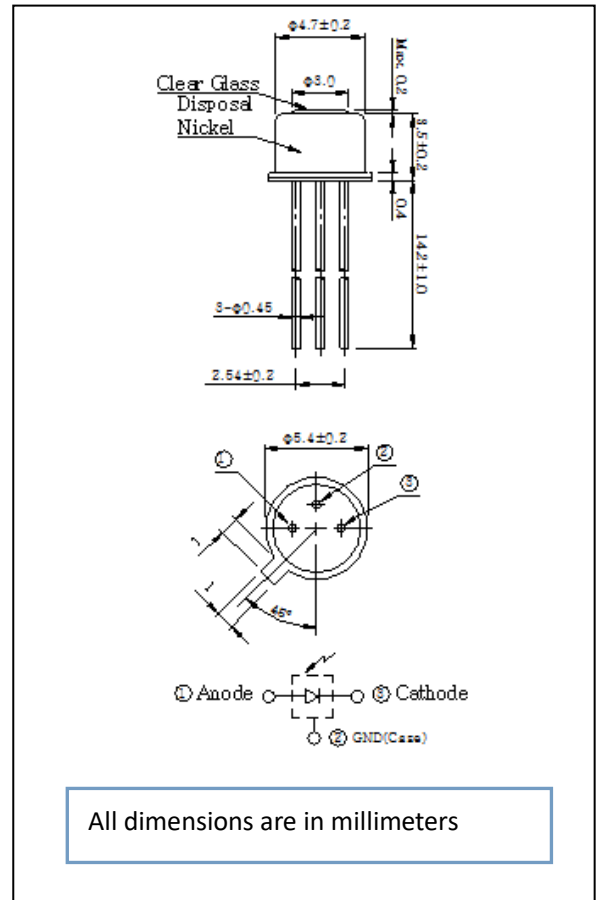


SiC-based Ultraviolet Detector



Description

SiC1.0TF-3 is broad band SiC based UV photodiode, it is Optimized for Ultra-violet , UVA, UVB and UVC wavelength. It can be easily selected With integral filters.

Features

- * High reliability in demanding environments
- * Good visible blindness

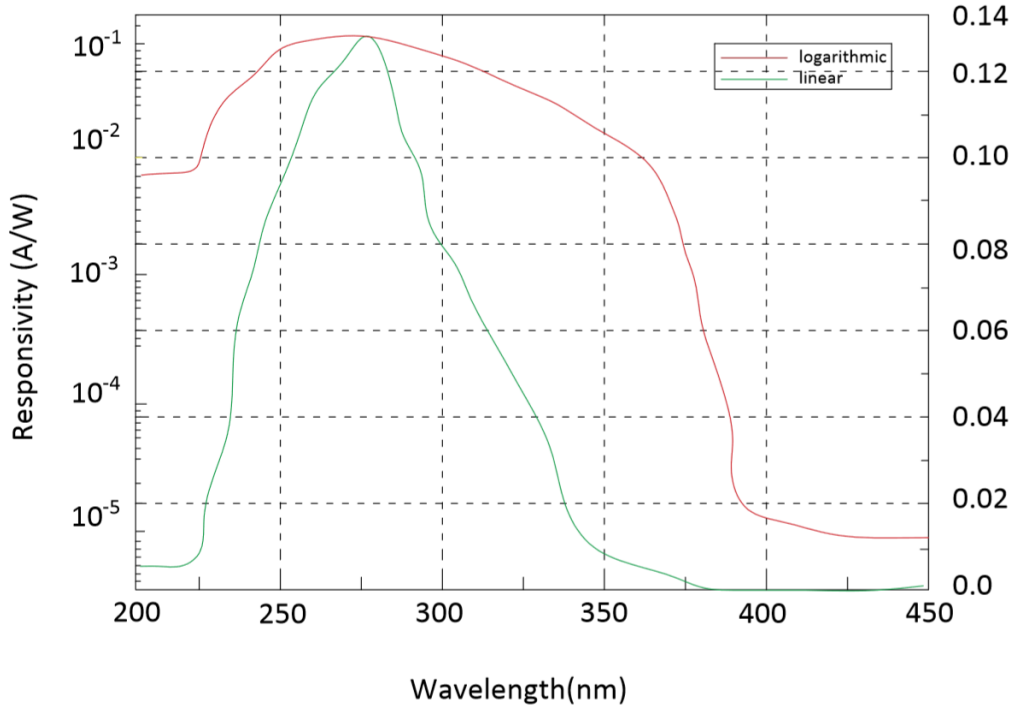
Applications

- * Sunlight exposure meter
- * Water purification facilities
- * UV power meter

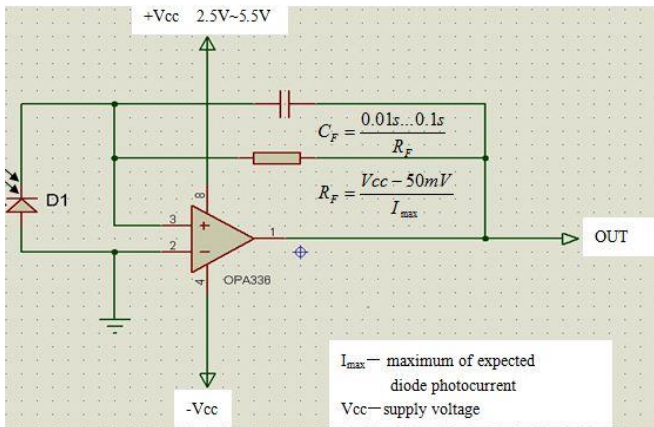
Specifications:

Parameter	Symbol	Min.	Typ.	Max.	Unit
Operation temperature range	T _{opt}	-25		+120	°C
Storage temperature range	T _{sto}	-40		+120	°C
Soldering temperature (3s)	T _{sol}		260		°C
Reverse voltage	V _r		-20		V
Chip size (active area)	A		1.0		mm ²
Dark current (V _r =-5V)	I _d			10	nA
Temperature coefficient	T _c		-0.1		%/°C
Capacitance (V _r =0V, f=1MHz)	C _j		97		pF
Wavelength of peak responsivity	λ_p		275		nm
Peak responsivity (@275nm)	R _{max}		0.13		A/W
Spectral response range (R=0.1*R _{max})	S _R	215		360	nm
UV-Visible rejection ratio(R _{max} /R _{400nm})	-	10 ⁴			-

Spectral response



Typical application circuit



Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice